

IN THE SPECIFICATION

Please replace the paragraph beginning at page 21, line 20, and continuing to page 22, with the following rewritten paragraph:

Referring to FIG.2, shown in cross section, is a printed and fire cured silver paste grid screen 9095 attached to silver-alloy thin film 80. Light 20 passes through glass substrate 51 to reach the doped semiconductor structure for the conversion of light to electromotive force (p-i-n junction layers 71, 70, 72). Light interacts with the p-i-n junction to generate negatively charged electrons and positively charged holes. Light that passes through the doped semiconductor structure for the conversion of light to electromotive force 70, 71, 72 reaches highly reflective silver-alloy thin film, or layer 80 and is reflected back through layers 70, 71, 72. At least a portion of the light reflected back through the p-i-n junction by highly reflective layer 80 generates negatively charged electrons and positively charged holes. Light reflected by layer 80 through p-i-n junction increase the amount of electricity generated by cell 40 for a given amount of light entering photo-voltaic cell 40.

Please replace the paragraph beginning at page 22, line 14 with the following rewritten paragraph:

In one embodiment of the invention reflective layer 80 is combined with grid 9095 to form the electrical grid contact on the side of solar voltaic cell 40 furthest from incident light 20.